

# The 4PP: Obsolete or Timeless

Walt Johnson  
KLA-Tencor



# Short History of the 4PP

- **1978 Tencor introduces the M-gage**
  - Replaced my +/- 10% Veeco 4PP with an M-Gage (4PP obsolete?)
- **1983 Prometrix Introduces dual configuration +/-1%**
  - Bought an OmniMap
- **1985 Prometrix reviews future**
  - Management decides 4PP has 2 yrs life
- **1994 Prometrix merges with Tencor**
  - Tencor management drops M-Gage, decides 4PP has 2 more yrs
- **1997 Tencor merges with KLA**
  - KLA management decides the 4PP has 2 more years

# The Status of the 4PP

- So where do we stand today?

# Markets addressed by the 4PP

- Metals

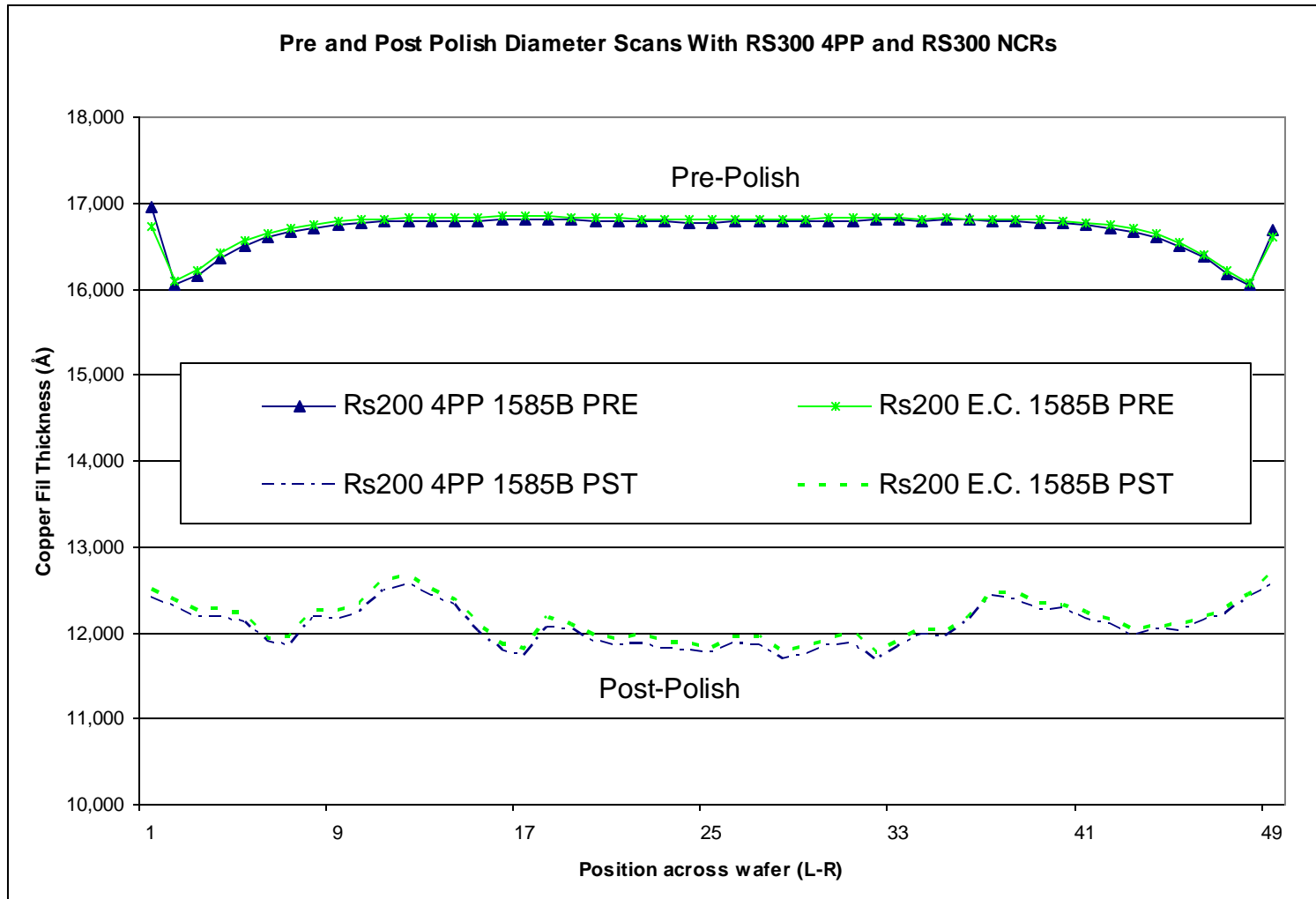
- Metal sheet resistance
- Metal thickness assuming a given resistivity
- Metal resistivity assuming a given thickness

- Ion Implant

- Dose monitoring (post anneal assuming a given anneal level)
- Ion activation (post anneal assuming a given dose level)

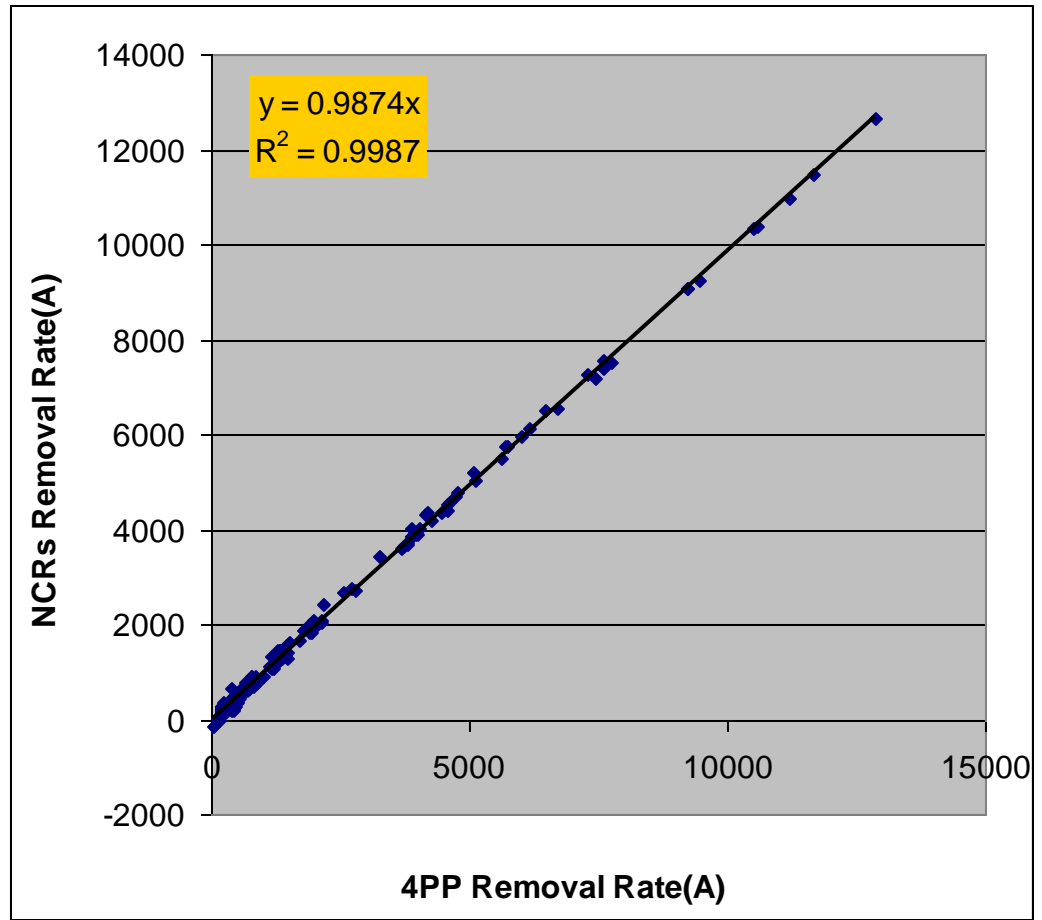
# NCRs (eddy current) Replaces 4PP for metals

(at least for thick metals on high resistance substrates)



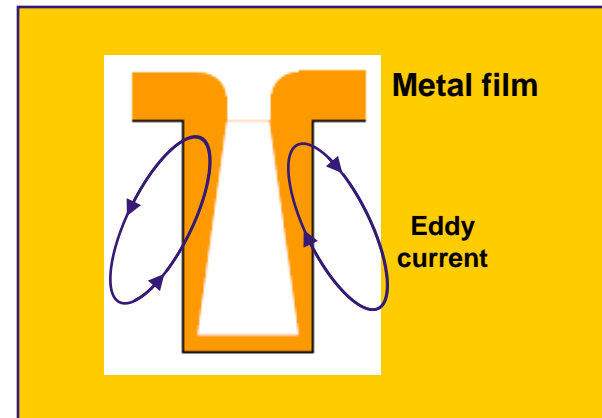
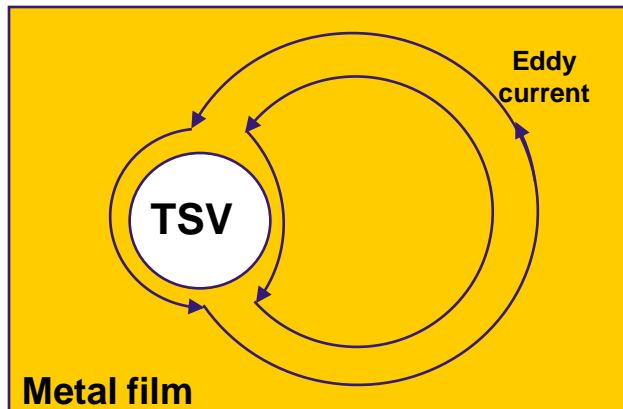
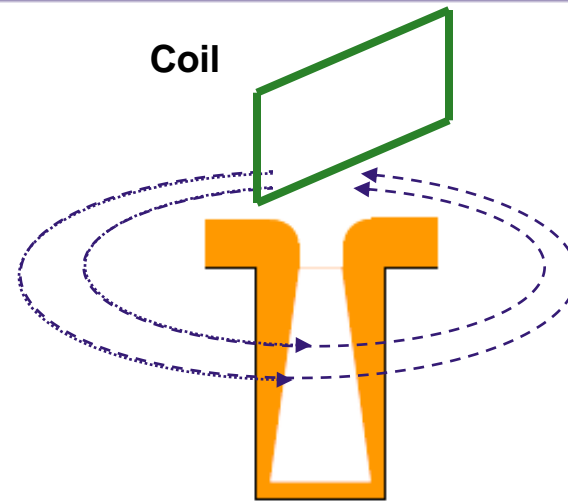
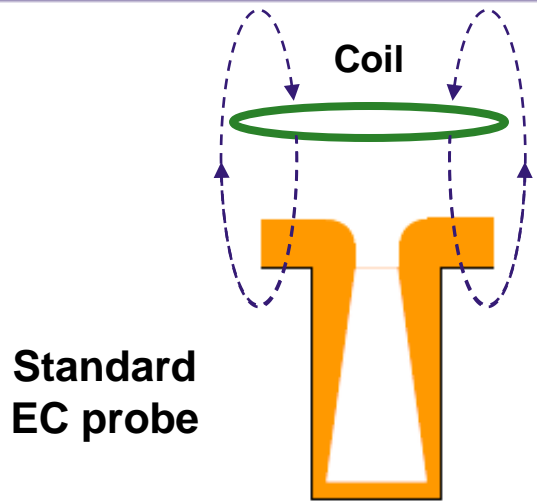
# Copper Removal Correlation

- Overall correlation between 4PP and NCRs (on multiple wafer sets)



# New Eddy Current Probe Development

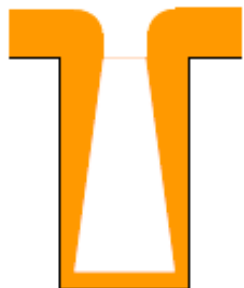
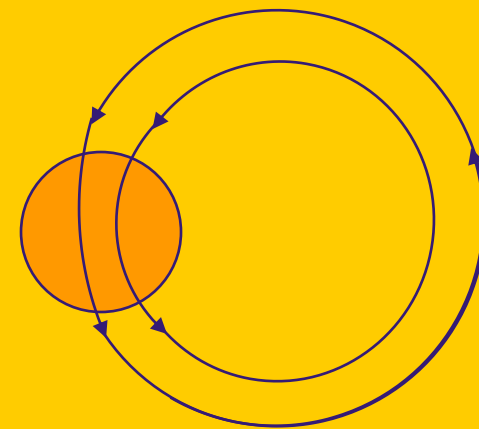
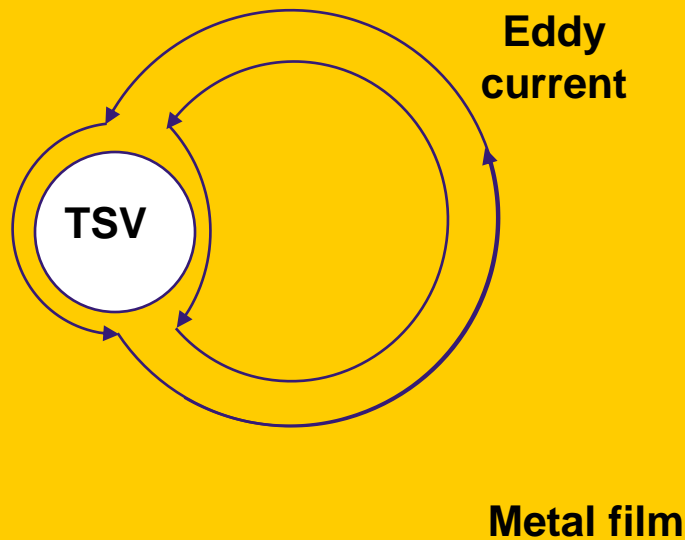
(Patent pending)



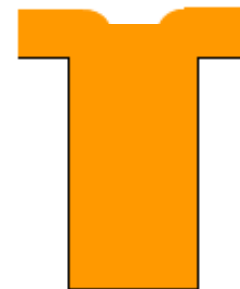
- The direction of eddy current by current probe is parallel to film surface and less sensitive to via sidewall coverage
- The direction of eddy current by new probe is perpendicular to film surface which should have better sensitivity

# Eddy Current Signal on Unfilled & Filled Via

- Filled and unfilled via shall show difference in eddy current signal



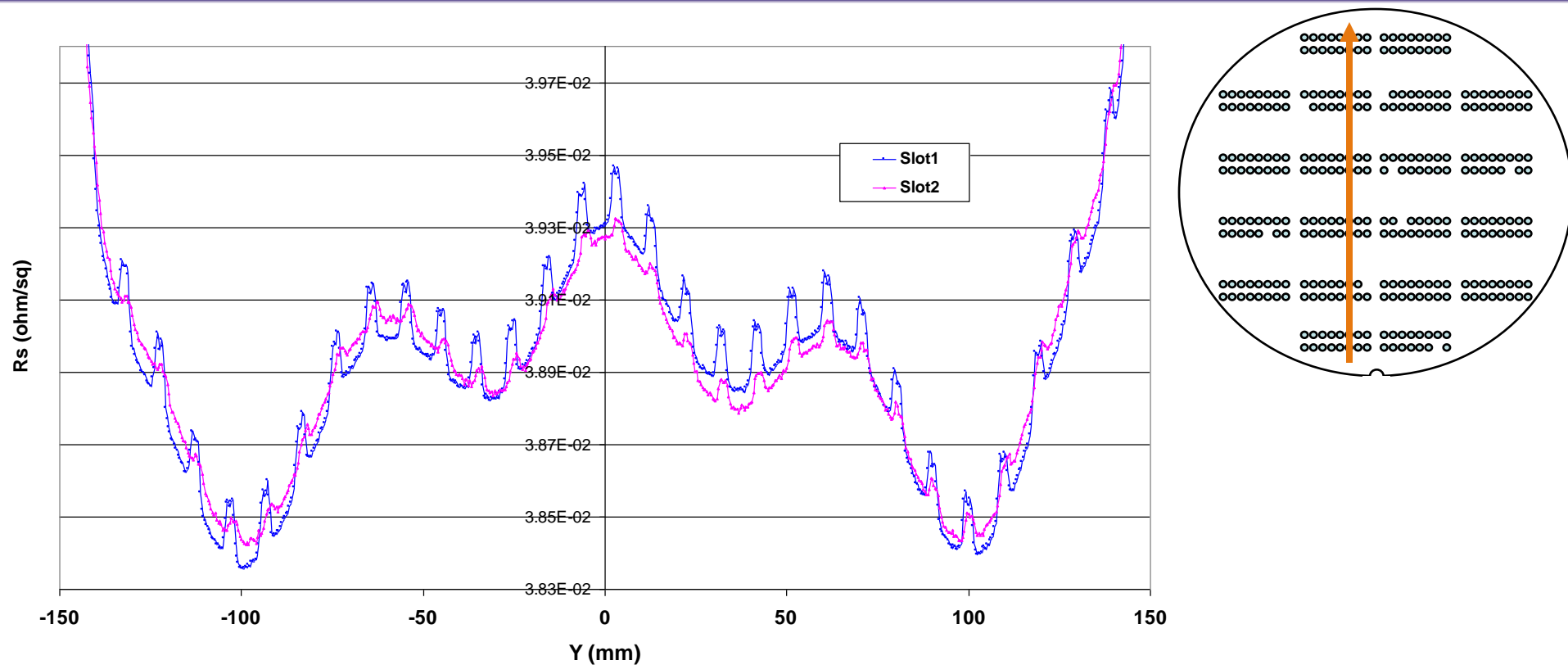
Unfilled TSV



Filled TSV

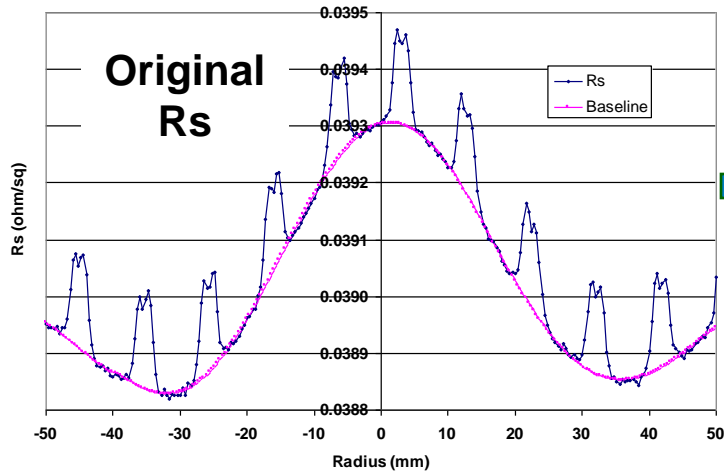


# Y-direction Diameter Scan (in arrow direction)

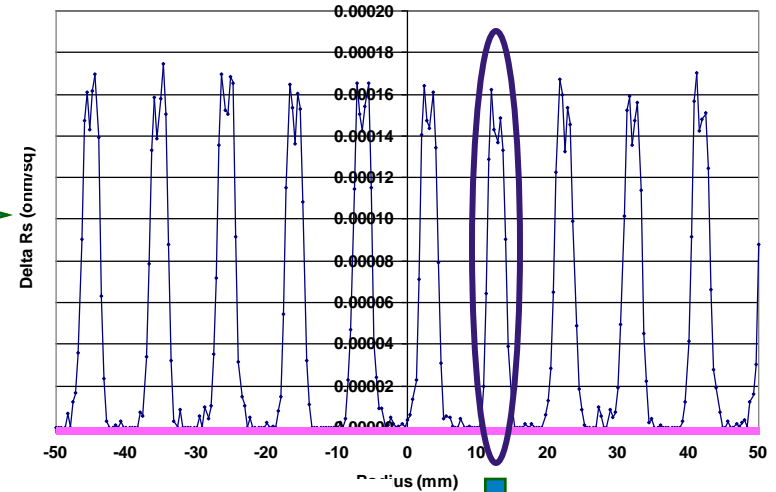


- Peak area correlates to via coverage
  - Repeated via peaks super-imposed on the global Rs non-uniform distribution

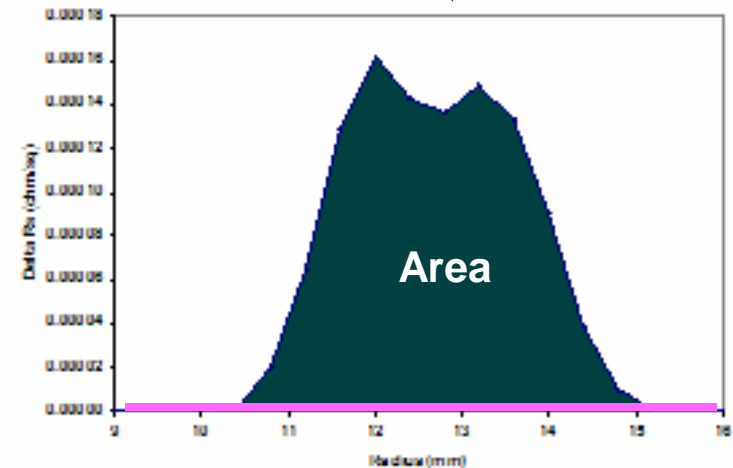
# Rs Peak Area Calculation Algorithm



**Eliminate  
Baseline  
Curve**



**Calculate  
Peak Area**



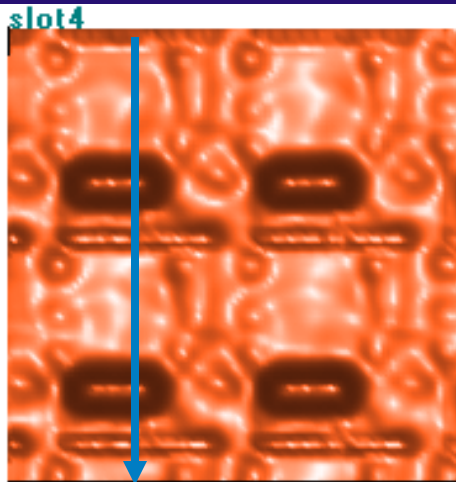
- Rs peak area correlates to via coverage

# Hi Density Rs Measurement in Die (Slot 4)

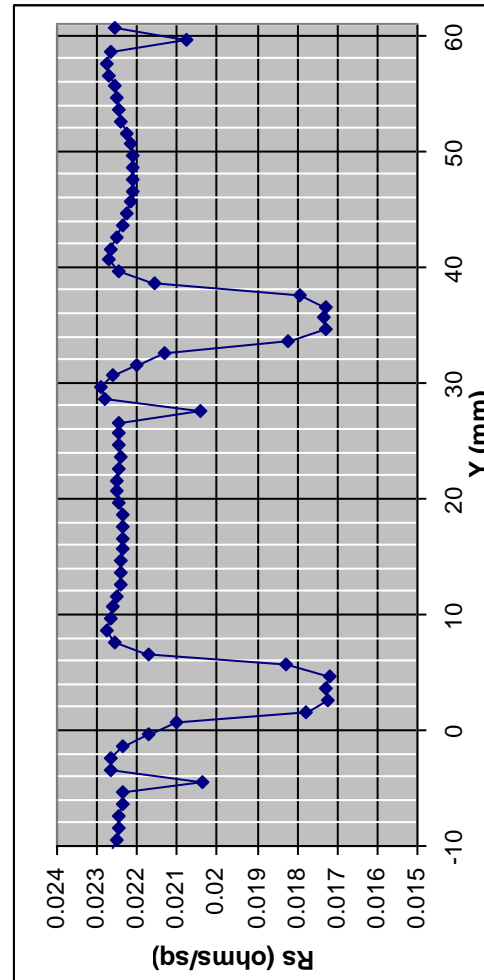
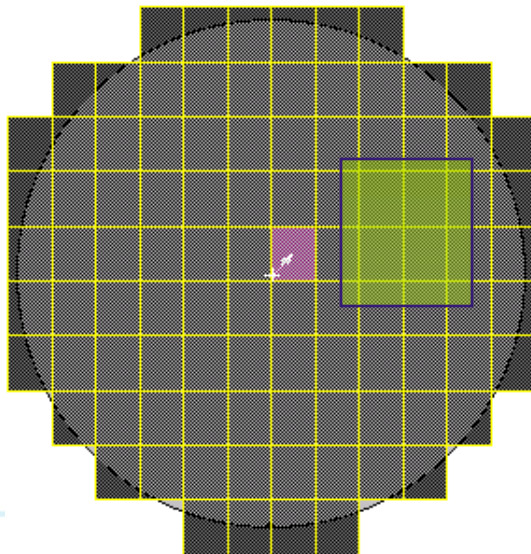
# Points: 4392  
 Max: 0.0234  
 Min: 0.017  
 Mean: 0.0221  
 STD: 0.0011  
 Center: (50.6,25.1)

**Percentile**

90.00	0.023
50.00	0.022
10.00	0.021

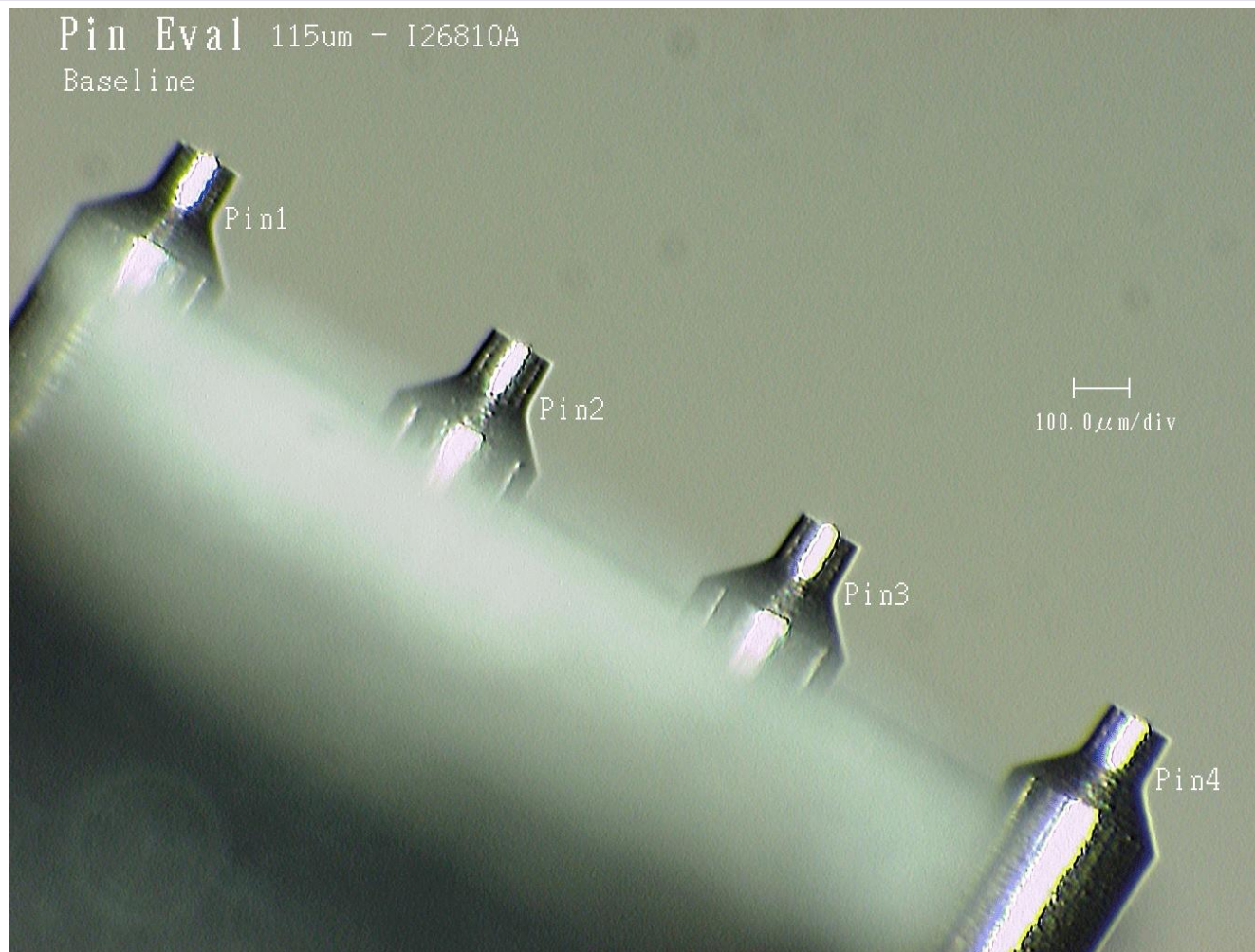


33 45 57 69

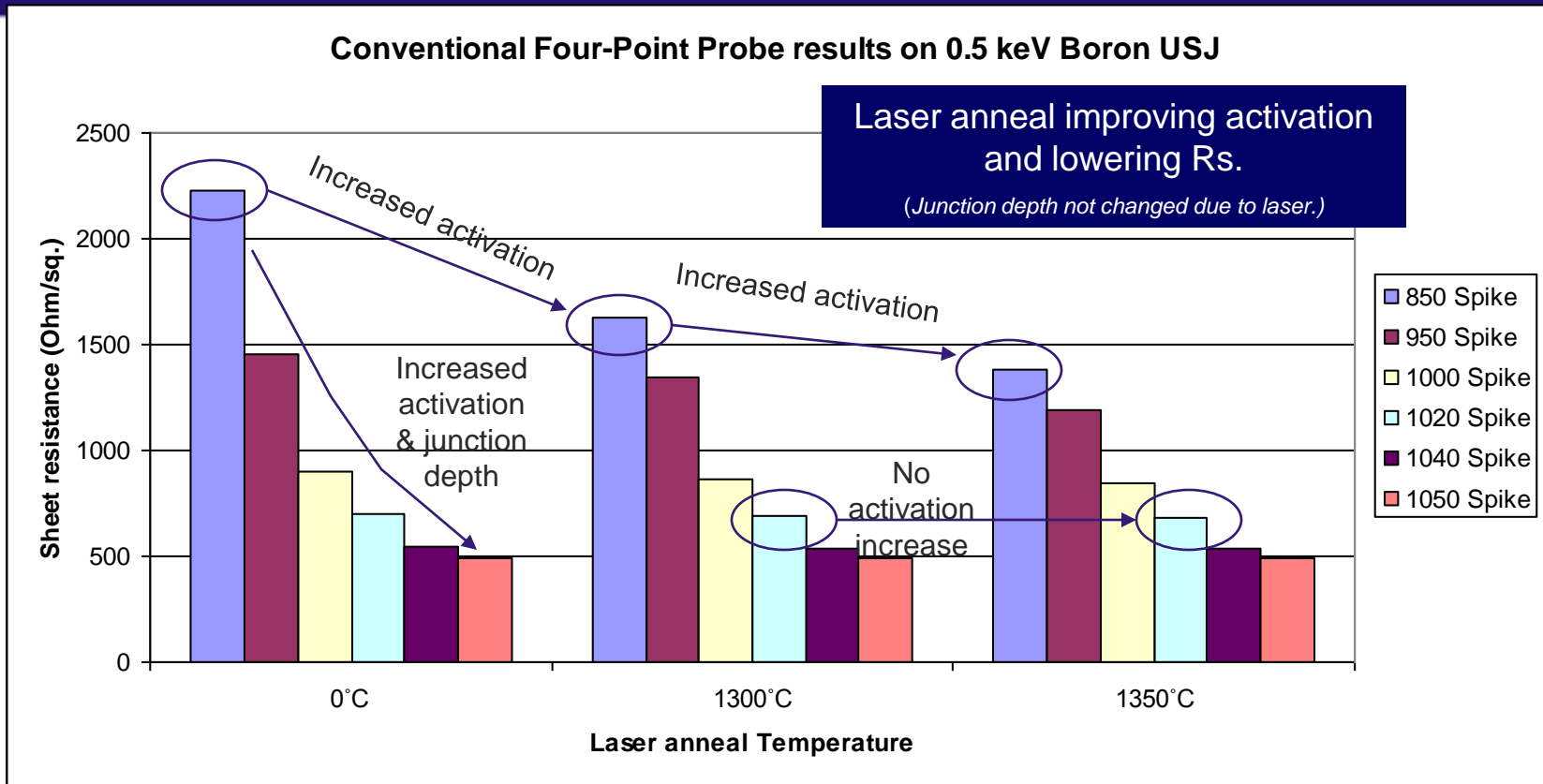


Depending on if Rs variations are of interest, recipe set up will need to be used to either measure those areas or avoid them.

# Improved USJ Measurements with Hx probes



# Activation Development & Control

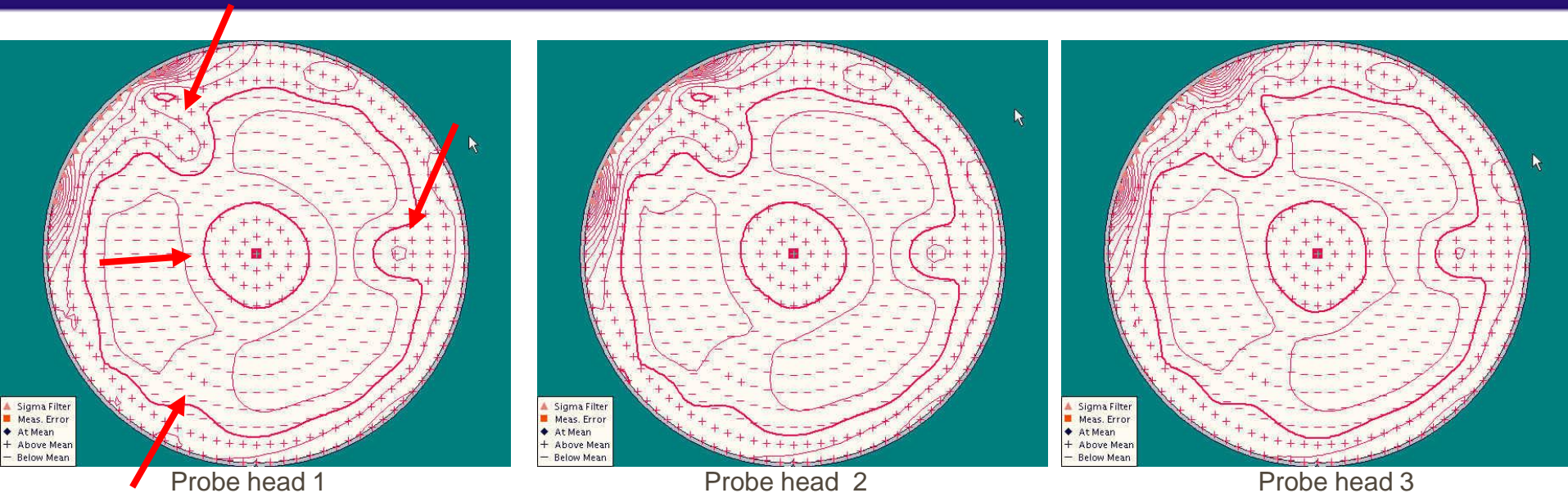


4PP provides sensitivity for process development & monitoring to detect small temperature fluctuations

Customer "A" data



# Discovering Annealer Problems on a 0.5 keV B+ implant



- High variations toward upper left edge of wafer
  - 14 points in area show measurement error or data outside sigma filter
- Center ring possibly due to thermocouple from annealer
- Three higher Rs regions around center possibly due to pedestal in annealer
- Excellent matching between probe heads, and results repeatability

Yield-limiting detail analysis of Anneal process equipment

Customer "C" data

# Long-Term Repeatability

Repeatability of Contour Map Results:

	BF2 1.5E14, 8 KEV 25 repeats	BF2 1E14, 5 KEV 25 repeats	As 1E14, 5 KEV 25 repeats	As 1E14, 3 KEV 25 repeats
Mean	1451	2508	1252	1613
% Stdev	0.16%	0.21%	0.14%	0.12%

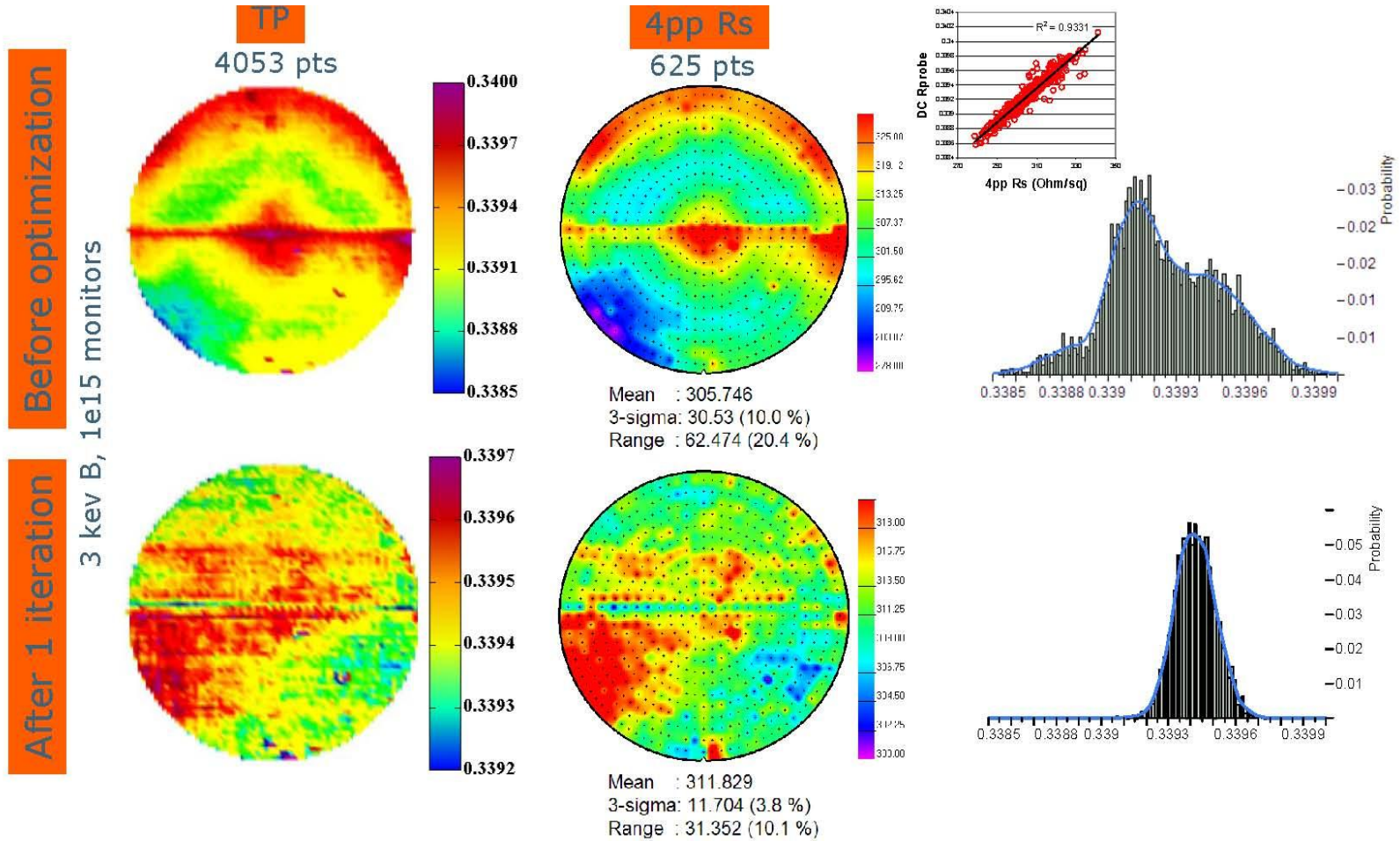
Repeatability on BF2 and Arsenic USJ implant maps is excellent

# Alternate Implant Monitoring Techniques

- IonScan
- Metrix e-beam
- TW
- SemiLab / FSM / Quantox (KLA-Tencor)
- Microwave ?

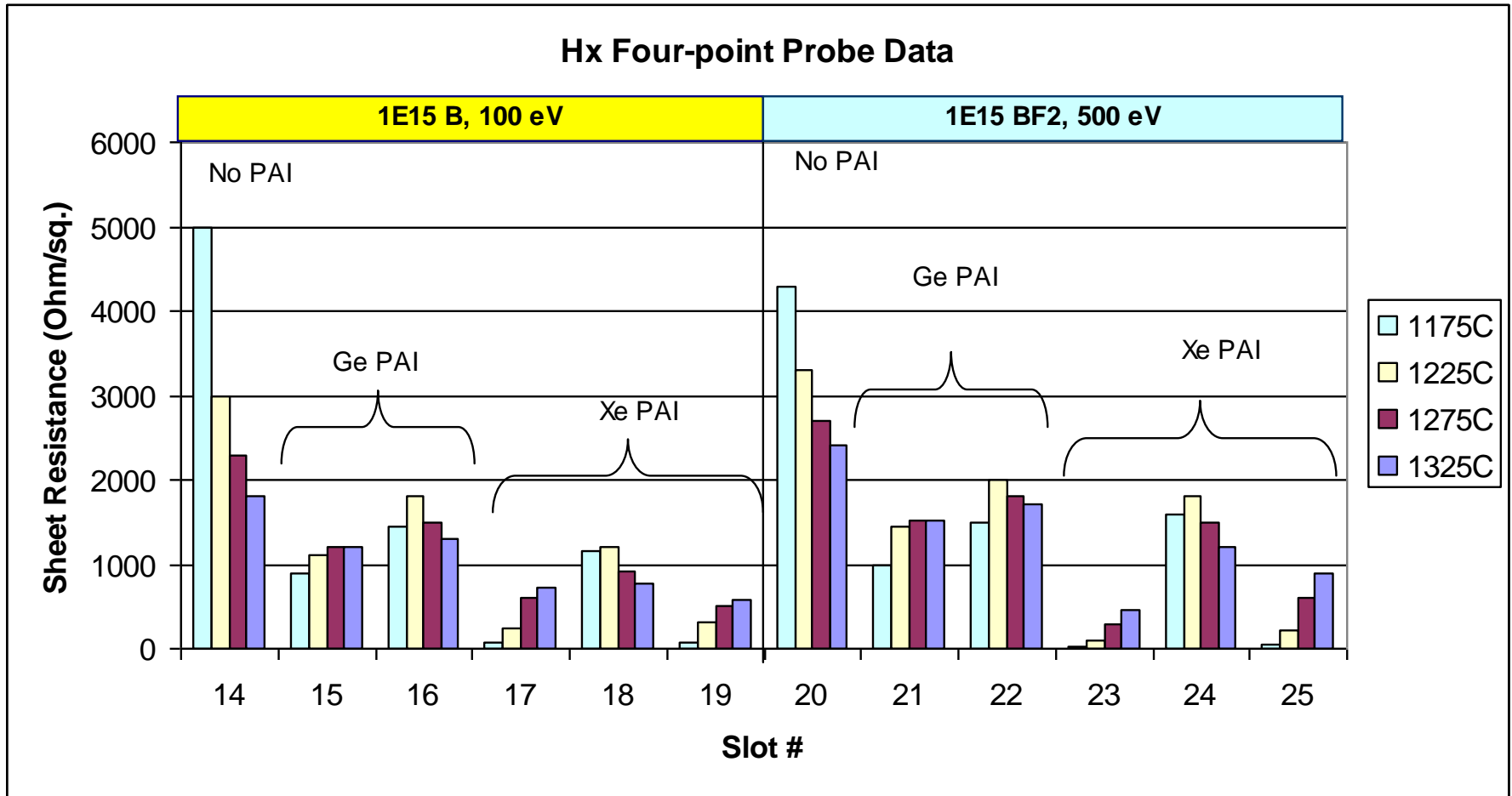


# TP to Rs Comparison

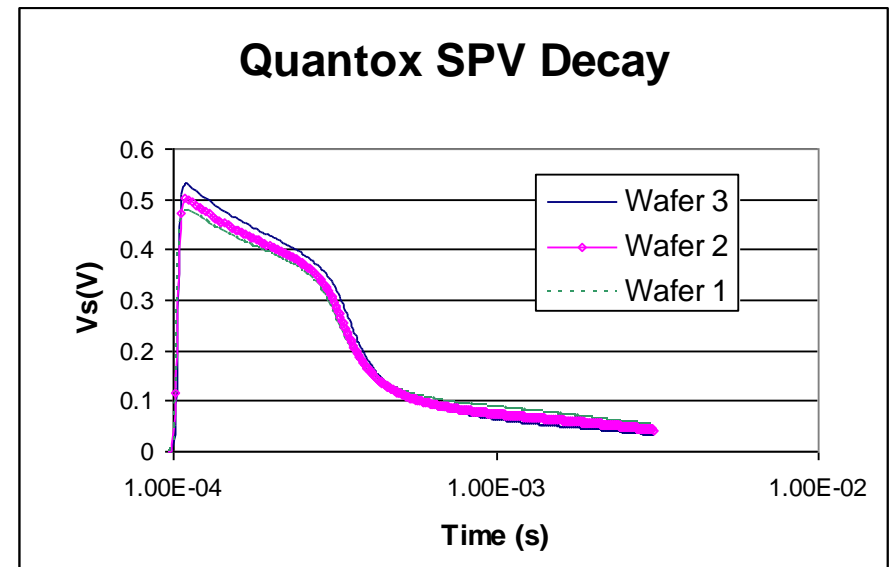
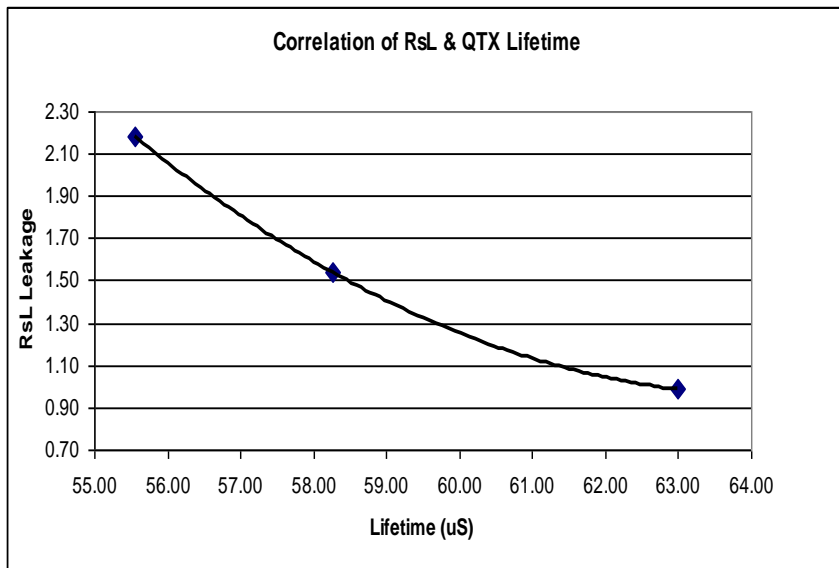


- Another example of laser anneal optimization with TP including comparison with Rs

# Junction Leakage Limits 4PP Usage



# SPV, JPV or LPV



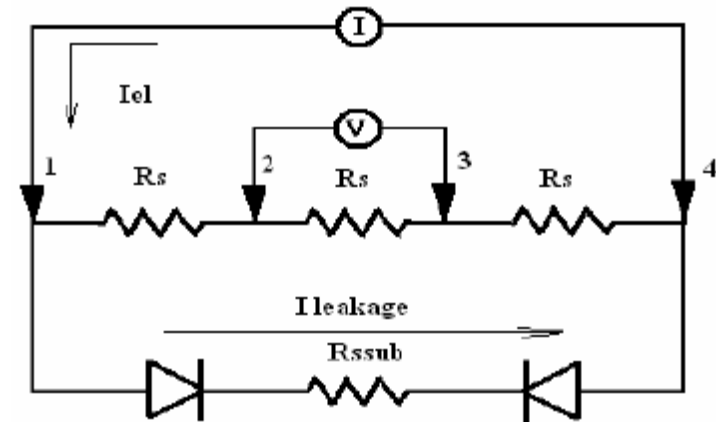
# 4PP Method

- The 4PP leakage through substrate can be modeled by following equivalent circuit

When  $I_{leakage} \ll I_{el}$ , the distribution of the measured potential is determined only by the current going through top layer with sheet resistance  $R_s$

$$V(x, y) = \frac{I_{EL} R_s}{2\pi} \ln \left( \frac{\sqrt{(x - x_1)^2 + (y - y_1)^2}}{\sqrt{(x - x_2)^2 + (y - y_2)^2}} \right)$$

Where  $I_{el}$  is the current, which flows through the probes 1 and 4 with coordinates  $(x_1, y_1)$  and  $(x_2, y_2)$  on the other. Approximately consider half of the area as forward bias diode, the other half as reverse biased diode.

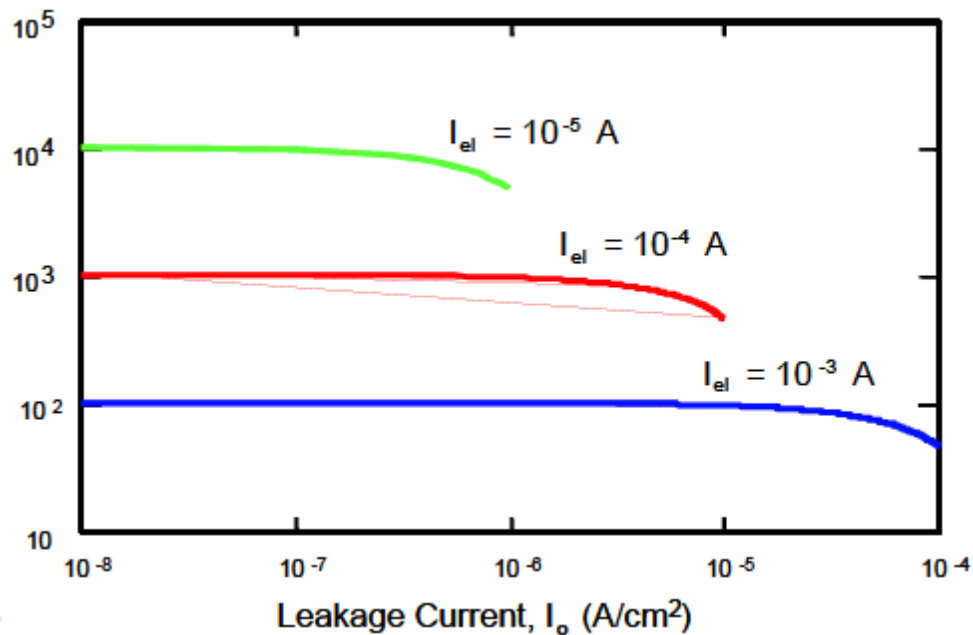


# 4PP Method (for leakage)

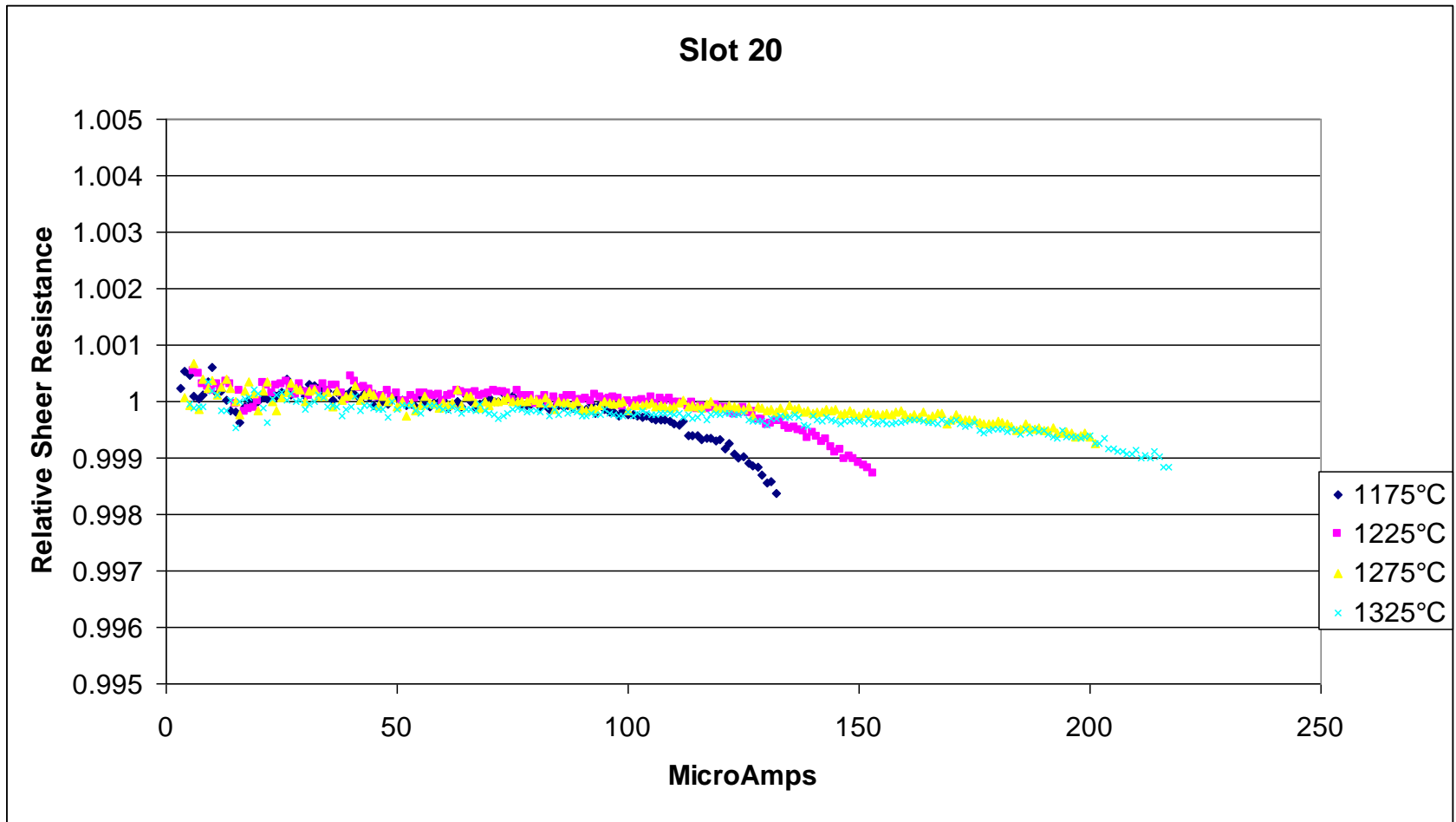
Measured  $R_s$  is a function of applied current for a fixed diode leakage density

$$I_{LEAK} = \iint_S j(x, y) dx dy = I_0 \iint_S \left[ \frac{\sqrt{(x-x_1)^2 + (y-y_1)^2}}{\sqrt{(x-x_2)^2 + (y-y_2)^2}} \exp\left(-\frac{q \cdot I_{EL} \cdot R_s}{2\pi kT}\right) - 1 \right] dx dy$$

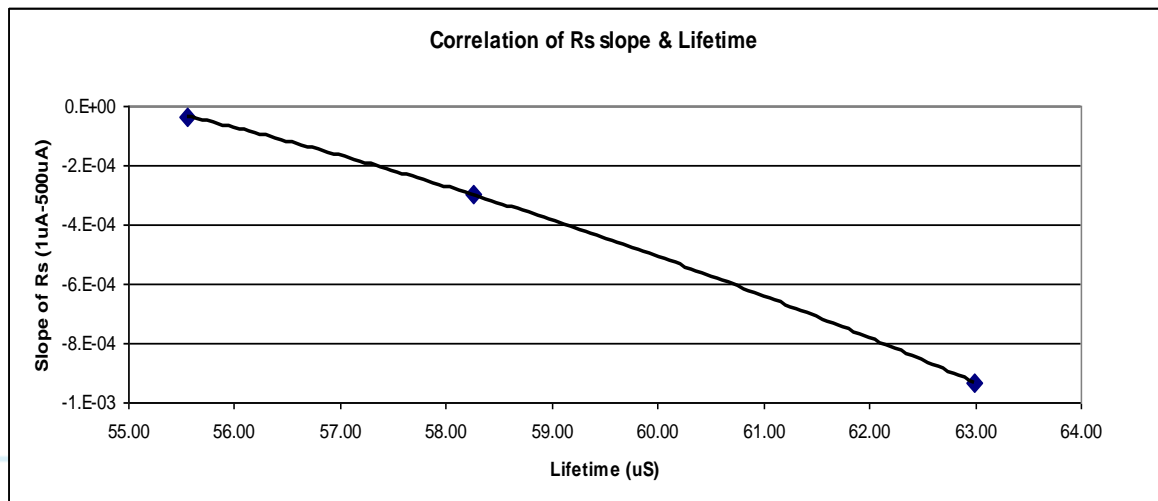
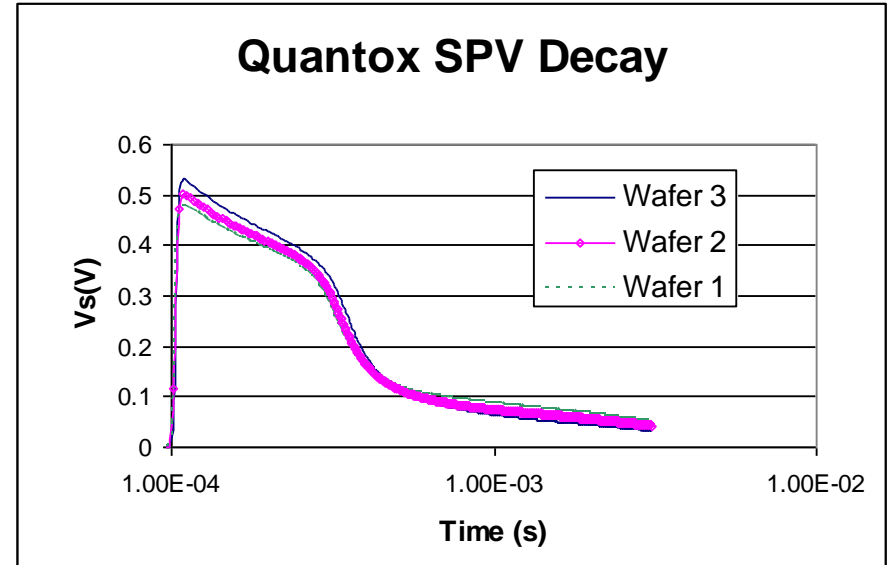
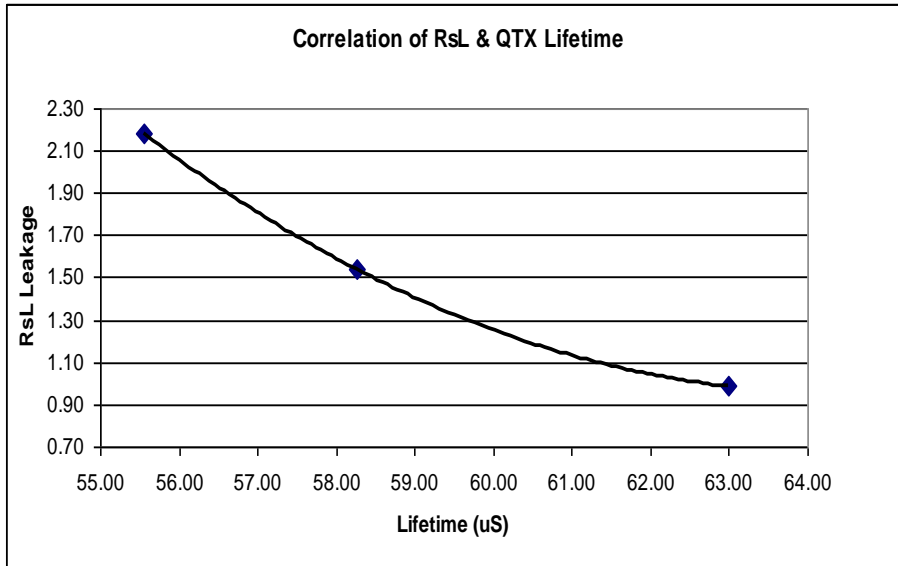
$$R_{s_{measured}} = \frac{\pi V_m}{\ln 2 I_{EL}}, \text{ where } V_m = \frac{\ln 2}{\pi} (I_{EL} - I_{Leak}) R_s$$



# Increased Leakage below 1275° Anneal



# Current Ramp Comparison to SPV



# Present Status of the 4PP

New (and older) technologies eddy current, TW, SPV etc. adding information on traditional 4PP applications

BUT!!!

4PP

Still not ready to give up